

RJK60S8DPK-M0

600V - 110A - SJ MOS FET
High Speed Power Switching

R07DS0644EJ0100

Rev.1.00

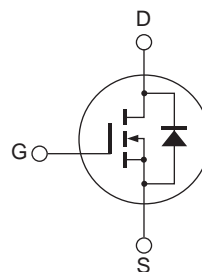
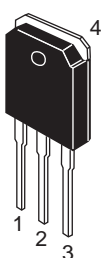
Apr 23, 2012

Features

- Superjunction MOSFET
- Low on-resistance
 $R_{DS(on)} = 0.045 \Omega$ typ. (at $I_D = 27.5 \text{ A}$, $V_{GS} = 10 \text{ V}$, $T_a = 25^\circ\text{C}$)
- High speed switching
 $t_f = 42 \text{ ns}$ typ. (at $I_D = 27.5 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_L = 10.9 \Omega$, $R_g = 10 \Omega$, $T_a = 25^\circ\text{C}$)

Outline

RENESAS Package code: PRSS0004ZH-A
(Package name:TO-3PSG)



1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

| Item | Symbol | Ratings | Unit |
|---|----------------------------------|-------------|--------------------|
| Drain to source voltage | V_{DSS} | 600 | V |
| Gate to source voltage | V_{GSS} | +30, -20 | V |
| Drain current | I_D ^{Note1} | 55 | A |
| | I_D ^{Note1} | 34.8 | A |
| Drain peak current | $I_{D(pulse)}$ ^{Note1} | 110 | A |
| Body-drain diode reverse drain current | I_{DR} ^{Note1} | 55 | A |
| Body-drain diode reverse drain peak current | $I_{DR(pulse)}$ ^{Note1} | 110 | A |
| Channel dissipation | P_{ch} ^{Note2} | 416.6 | W |
| Channel to case thermal impedance | θ_{ch-c} | 0.3 | $^\circ\text{C/W}$ |
| Channel temperature | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Notes: 1. Limited by T_{ch} max.

2. Value at $T_c = 25^\circ\text{C}$

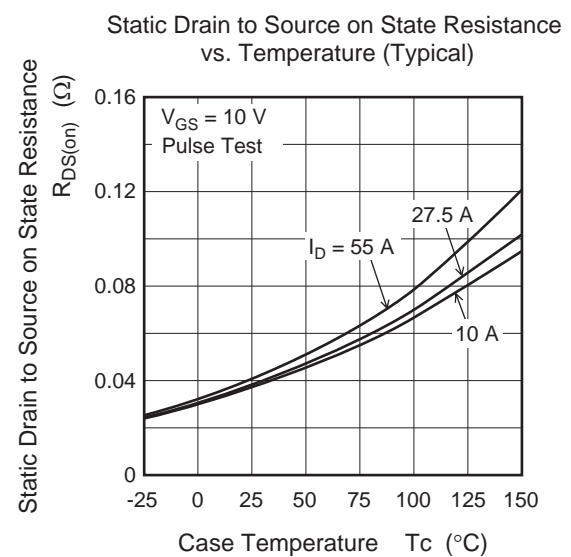
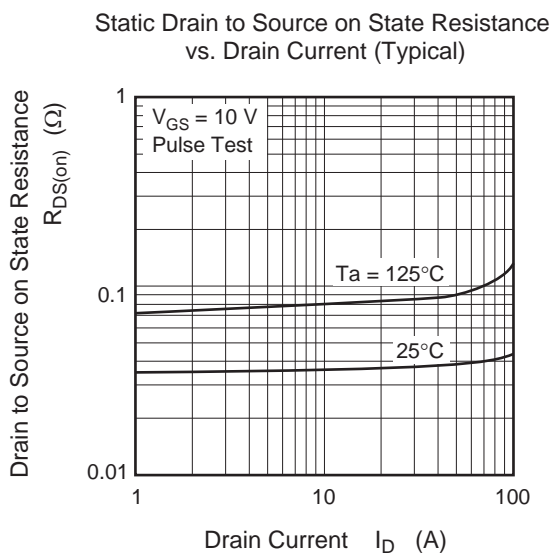
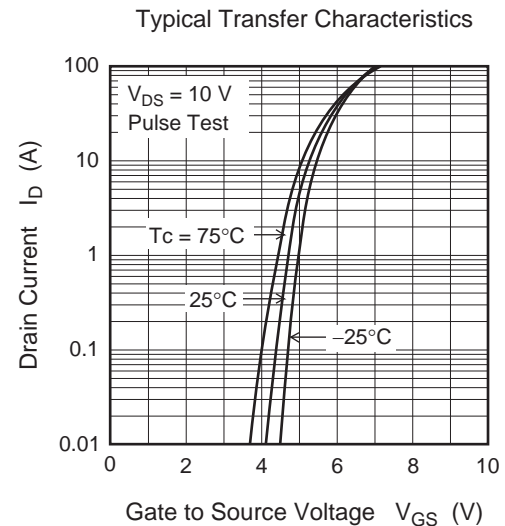
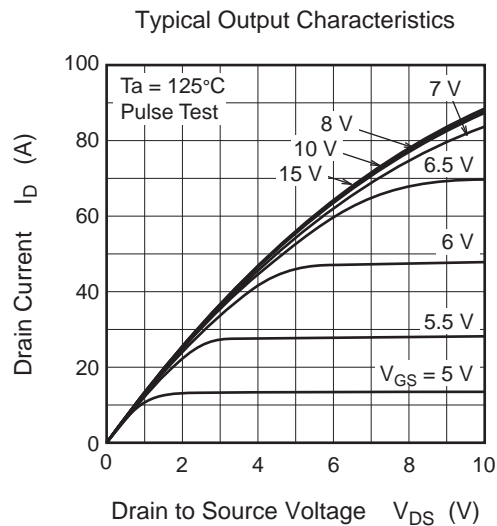
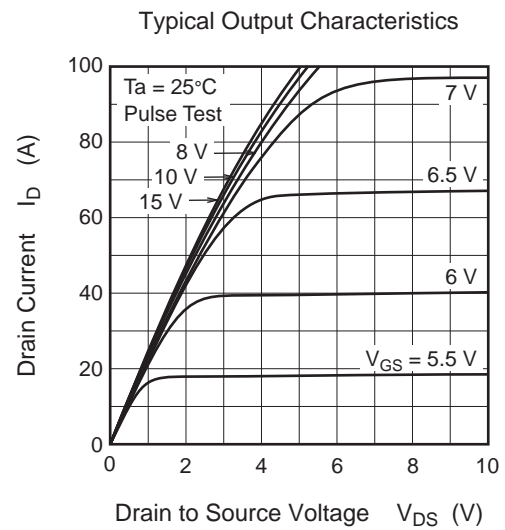
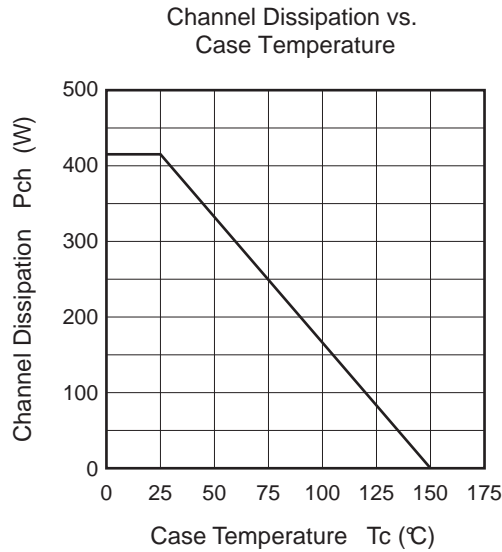
Electrical Characteristics

(Ta = 25°C)

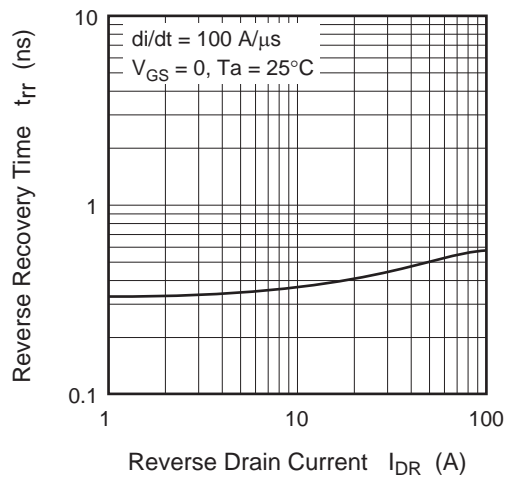
| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|--|---------------|-----|-------|-----------|---------------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 600 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 1 | mA | $V_{DS} = 600 \text{ V}$, $V_{GS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ± 0.1 | μA | $V_{GS} = +30\text{V}$, -20 V , $V_{DS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 3 | — | 5 | V | $V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 0.045 | 0.056 | Ω | $I_D = 27.5 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4} |
| | $R_{DS(on)}$ | — | 0.117 | — | Ω | Ta = 150°C $I_D = 27.5 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4} |
| Gate resistance | Rg | — | 1.0 | — | Ω | f = 1 MHz $V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$ |
| Input capacitance | Ciss | — | 5200 | — | pF | $V_{DS} = 25 \text{ V}$ |
| Output capacitance | Coss | — | 7000 | — | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | — | 23 | — | pF | f = 100 kHz |
| Turn-on delay time | $t_{d(on)}$ | — | 46 | — | ns | $I_D = 27.5 \text{ A}$ |
| Rise time | t_r | — | 50 | — | ns | $V_{GS} = 10 \text{ V}$ |
| Turn-off delay time | $t_{d(off)}$ | — | 123 | — | ns | $R_L = 10.9 \Omega$ |
| Fall time | t_f | — | 42 | — | ns | Rg = 10 Ω |
| Total gate charge | Qg | — | 82 | — | nC | $V_{DD} = 480 \text{ V}$ |
| Gate to source charge | Qgs | — | 31 | — | nC | $V_{GS} = 10 \text{ V}$ |
| Gate to drain charge | Qgd | — | 22 | — | nC | $I_D = 55 \text{ A}$ |
| Body-drain diode forward voltage | V_{DF} | — | 1.0 | 1.6 | V | $I_F = 55 \text{ A}$, $V_{GS} = 0$ ^{Note4} |
| Body-drain diode reverse recovery time | t_{rr} | — | 540 | — | ns | $I_F = 55 \text{ A}$ |
| Body-drain diode reverse recovery current | I_{rr} | — | 28 | — | A | $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ |
| Body-drain diode reverse recovery charge | Q_{rr} | — | 9.3 | — | μC | |

Notes: 4. Pulse test

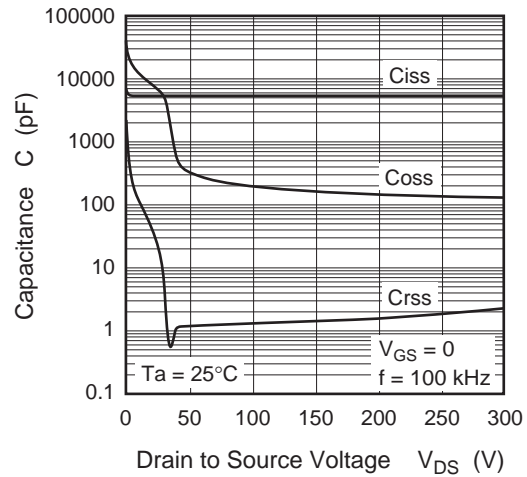
Main Characteristics



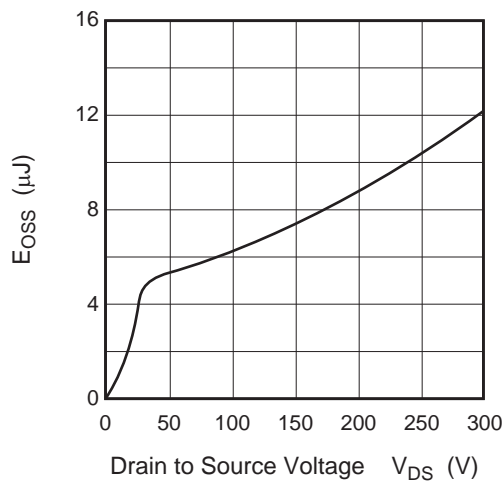
Body-Drain Diode Reverse Recovery Time (Typical)



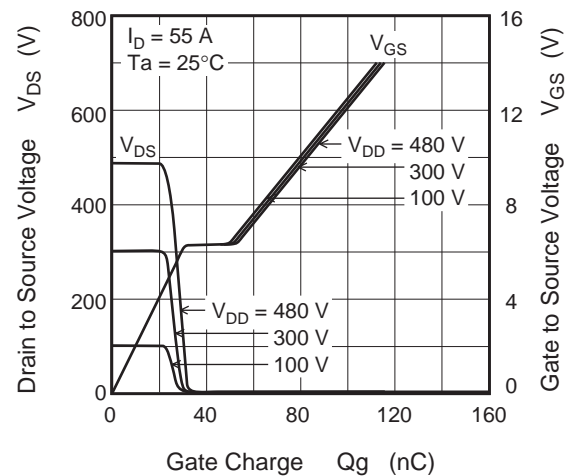
Typical Capacitance vs. Drain to Source Voltage



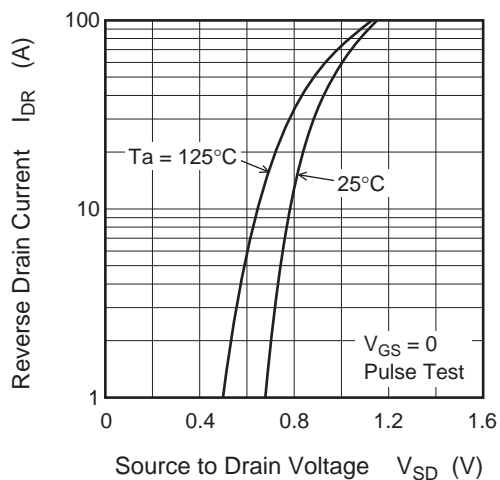
C_{OSS} Stored Energy (Typical)



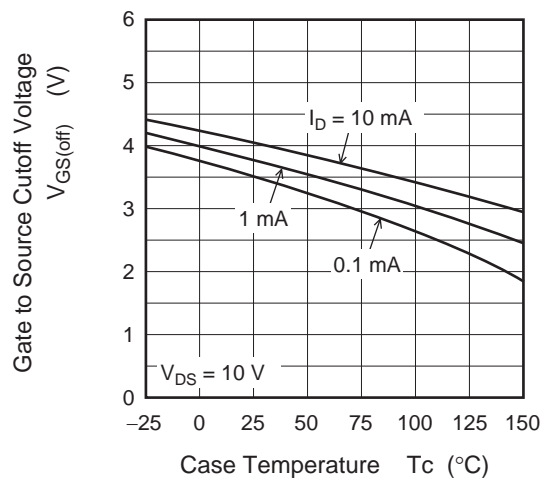
Dynamic Input Characteristics (Typical)



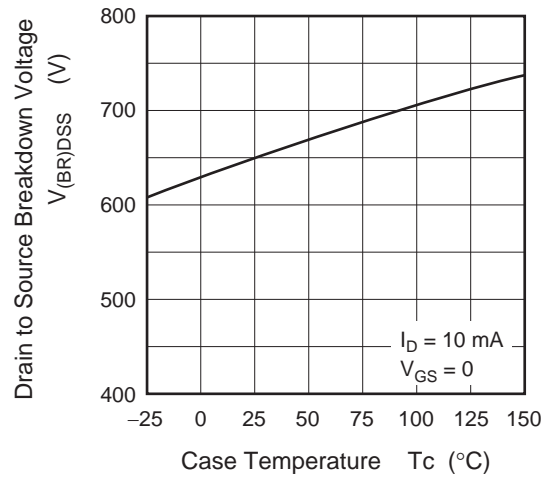
Reverse Drain Current vs. Source to Drain Voltage (Typical)



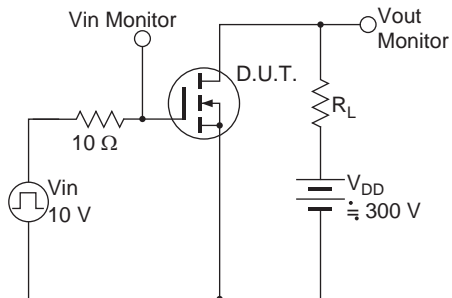
Gate to Source Cutoff Voltage vs. Case Temperature (Typical)



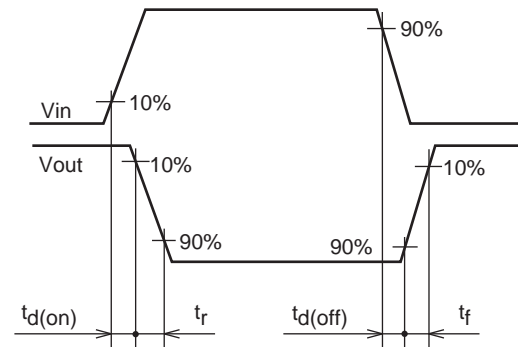
Drain to Source Breakdown Voltage
vs. Case Temperature (Typical)



Switching Time Test Circuit



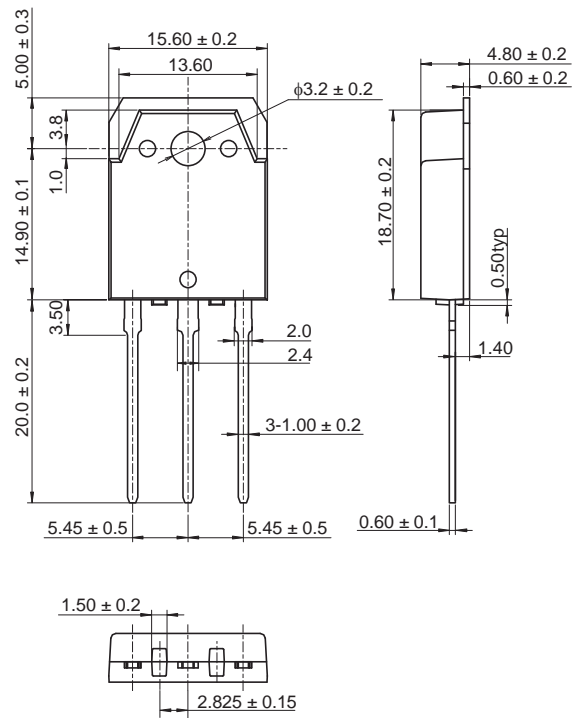
Waveform



Package Dimension

| Package Name | JEITA Package Code | RENESAS Code | Previous Code | MASS[Typ.] |
|--------------|--------------------|--------------|------------------|------------|
| TO-3PSG | — | PRSS0004ZH-A | TO-3PSG/TO-3PSGV | 3.7g |

Unit: mm



Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK60S8DPK-M0#T0 | 360 pcs | Box (Tube) |

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